

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S130	105996	sos near2 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/23 15:40
S129	3	(sapphire near2 "on" near2 silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/23 15:40
S133	0	sos! near2 substrate near10 (gan or gallium near2 nitride) near10 epitax\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/23 15:41
S132	29	sos near2 substrate near10 (gan or gallium near2 nitride) near10 epitax\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/23 15:41
S131	246	sos near2 substrate near10 (gan or gallium near2 nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/23 15:41
S134	3	sos! near2 substrate near10 (gan or gallium near2 nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/23 15:45
S135	7	sos! near10 (gan or gallium near2 nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/23 16:07
S136	2	sos! same (gan or gallium near2 nitride) near10 epitax\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/23 16:09
S137	17	sos! and (gan or gallium near2 nitride) near10 epitax\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/23 16:12

S13 9	2	(sos! or "silicon-on-sapphire") same (gan or gallium near2 nitride) near10 epitax\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/23 16:13
S13 8	22	(sos! or "silicon-on-sapphire") and (gan or gallium near2 nitride) near10 epitax\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/23 16:13
S14 0	54	(sos! or "silicon-on-sapphire") same (gan or gallium near2 nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/23 16:17
S14 1	8	(sos! or "silicon-on-sapphire") same (gan or gallium near2 nitride) and remov\$5 near10 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/23 16:39
S14 3	28	sapphire near10 silicon near10 layered	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/23 16:46
S14 2	21	sapphire near10 silicon near10 layered near2 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/23 16:46
S14 4	10	sapphire near10 silicon near10 layered and (gan or gallium near2 nitride or "iii-v")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/23 16:49
S14 9	0	("sapphire-on-silicon" or "sos") near10 (gan or gallium near2 nitride or "iii-v") near10 epitax\$6 and remov\$6 near10 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/23 16:50
S14 7	227	("sapphire-on-silicon" or "sos") near10 (gan or gallium near2 nitride or "iii-v") near10 epitax\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/23 16:50
S14 6	690	("sapphire-on-silicon" or "sos") same (gan or gallium near2 nitride or "iii-v") near10 epitax\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/23 16:50

S14 5	6134	("sapphire-on-silicon" or "sos") same (gan or gallium near2 nitride or "iii-v")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/23 16:50
S15 0	1	("sapphire-on-silicon" or "sos") near10 (gan or gallium near2 nitride or "iii-v") near10 epitax\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/23 16:51
S14 8	106	("sapphire-on-silicon" or "sos") near10 (gan or gallium near2 nitride or "iii-v") near10 epitax\$6 and remov\$6 near10 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/23 16:51
S15 3	2	two near1 sid\$3 near4 deposit\$4 and "117"/\$4.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/24 14:20
S15 2	0	("sapphire-on-silicon" or "sapphire on silicon") near10 (gan or gallium near2 nitride or "iii-v")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/24 14:20
S15 1	25	("sapphire-on-silicon" or "sos") near10 (gan or gallium near2 nitride or "iii-v")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/24 14:20
S46	2	two near1 sid\$3 near4 deposit\$4 and "117"/\$4.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/24 14:20
S15 4	2	"5081519".pn. and epitax\$7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 18:28
S16 1	6	epitax\$6 near10 (gan or gallium near2 nitride) same (sapphire and silicon) near10 substrate and @Py<"2002"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 18:47
S16 0	221	epitax\$6 near10 (gan or gallium near2 nitride) same (sapphire and silicon) near10 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 18:47

S15 9	836	epitax\$6 near10 (gan or gallium near2 nitride) and (sapphire and silicon) near10 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 18:47
S15 8	3	"6428722".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 18:47
S15 7	0	epitax6 near10 (gan or gallium near2 nitride) and (sapphire and silicon) near10 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 18:47
S15 6	0	epitax6 near10 (gan or gallium near2 nitride) same (sapphire and silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 18:47
S15 5	3	"6428722".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 18:47
S16 2	2	"6649287".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 18:53
S16 6	58	epitax\$7 near10 (gallium near2 nitride or gan) near10 silicon near2 sapphire near10 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 19:01
S16 5	435	(gallium near2 nitride or gan) near10 silicon near2 sapphire near10 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 19:01
S16 4	537	(gallium near2 nitride or gan) near10 silicon near2 sapphire	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 19:01
S16 3	2	"6617060".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 19:01

L37	2	"6617060".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 11:51
L39	1	"6617060".pn. and epitax\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 12:09
L40	0	tishcler.in. and polish\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 12:11
L44	915	(silicon adj "on" adj sapphire or sos or sapphire adj "on" adj silicon) near10 substrate same (gan or gallium near2 nitride) and epitax\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 12:13
L43	1212	(silicon adj "on" adj sapphire or sos or sapphire adj "on" adj silicon) near10 substrate same (gan or gallium near2 nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 12:13
L48	4845	(silicon near2 sapphire or sos! or sapphire near2 silicon) near10 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 12:14
L47	1650	(silicon adj "on" adj sapphire or sos! or sapphire adj "on" adj silicon) near10 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 12:14
L46	1	(silicon adj "on" adj sapphire or sos! or sapphire adj "on" adj silicon) near10 substrate same (gan or gallium near2 nitride) near10 epitax\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 12:14
L45	212	(silicon adj "on" adj sapphire or sos or sapphire adj "on" adj silicon) near10 substrate same (gan or gallium near2 nitride) near10 epitax\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 12:14
L42	241550	(silicon near2 sapphire or sos or sapphire near2 silicon) near10 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 12:14

L41	239492	(silicon adj "on" adj sapphire or sos or sapphire adj "on" adj silicon) near10 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 12:14
L49	52	(silicon adj "on" adj sapphire or sos! or sapphire adj "on" adj silicon) near10 substrate same (gan or gallium near2 nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 12:16
L51	37	(silicon adj "on" adj sapphire or sos! or sapphire adj "on" adj silicon) near10 substrate near15 temperature	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 12:22
L50	15	(silicon adj "on" adj sapphire or sos! or sapphire adj "on" adj silicon) near10 substrate same "iii-v"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 12:22
L52	2	"5679152".pn. and epitax\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 13:12
L38	2	"5679152".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 13:12
S32	0	udea near2 tetsuzo.in. and (warp\$ or bow\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 15:20
L53	0	udea near2 tetsuzo.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 15:20
L55	14	ueda near2 tetsuzo.in. and sapphire near2 silicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 15:21
L54	15	ueda near2 tetsuzo.in. and (warp\$ or bow\$6)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/30 15:21